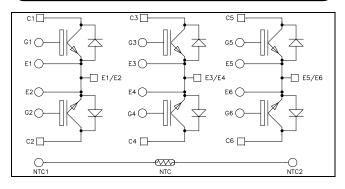
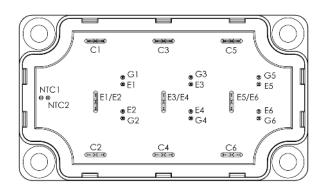


Triple Dual Common Source Trench + Field Stop IGBT4 Power module





Absolute maximum ratings

$V_{CES} = 1200V$ $I_{C} = 120A$ @ Tc = 80°C

Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
 - Symmetrical design
- Kelvin emitter for easy drive
 - Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
I _C	Continuous Collector Current	$T_c = 25^{\circ}C$	140	
	Continuous Conector Current	$T_c = 80^{\circ}C$	120	Α
I _{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	200	
V_{GE}	Gate – Emitter Voltage		±20	V
P _D	Maximum Power Dissipation	$T_c = 25^{\circ}C$	517	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	200A @ 1150V	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Electri	cal Characteristics		I				
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} =$	= 1200V			250	μA
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.8	2.15	V
V _{CE(sat)}	Conector Emitter saturation voltage	$I_{\rm C} = 100 {\rm A}$	$T_{j} = 150^{\circ}C$		2.15		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 3.4 \text{mA}$		5.2	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE}$	= 0V			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			6.2			
Coes	Output Capacitance				0.4		nF	
C _{res}	Reverse Transfer Capacitance	f = 1 MHz			0.35			
Q _G	Gate charge	$V_{GE} = \pm 15V$; $V_{GE} = 100A$	$V_{GE} = \pm 15V$; $V_{CE} = 600V$ $I_{C} = 100A$		0.85		μC	
T _{d(on)}	Turn-on Delay Time	Inductive Switc	hing (25°C)		130		ns	
T _r	Rise Time	$V_{GE} = \pm 15V$			20			
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 100A$			300			
T _f	Fall Time	$R_G = 7.5\Omega$			45			
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C)			150			
Tr	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$			35		ns	
T _{d(off)}	Turn-off Delay Time	$I_C = 100A$			350			
T _f	Fall Time	$R_G = 7.5\Omega$			80			
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25^{\circ}C$		5		mI	
Lon	Tuni-on Switching Energy	$V_{Bus} = 600V$	$V_{Bus} = 600V$ $T_J = 150^{\circ}C$	$T_{\rm J} = 150^{\circ}{\rm C}$		10.5		mJ
E _{off}	Turn-off Switching Energy	$I_{\rm C} = 100 {\rm A}$	$T_J = 25^{\circ}C$		5.5		mJ	
Loff	run-on Switching Energy	$R_G = 7.5\Omega$	$T_{\rm J} = 150^{\circ}{\rm C}$		9.5		1115	
I _{sc}	Short Circuit data	$V_{GE} \le 15V ; V_{Bu}$ $t_p \le 10\mu s ; T_j = 1$			400		А	

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		-	1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$			250	μA
I _F	DC Forward Current		$Tc = 80^{\circ}C$		120		Α
V	Diode Forward Voltage	$I_{\rm F} = 100 {\rm A}$	$T_i = 25^{\circ}C$		1.9	2.4	V
$V_{\rm F}$	Diode Forward Voltage	$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.85		v
t	Reverse Recovery Time	Т	$T_j = 25^{\circ}C$		155		ns
t _{rr}	Reverse Recovery Time		$T_{j} = 150^{\circ}C$		300		115
0	Reverse Recovery Charge	$V_{\rm R} = 600 {\rm V}$	$T_j = 25^{\circ}C$		9.3		uС
Qrr			$T_{i} = 150^{\circ}C$		20		μC
E _{rr}	Reverse Recovery Energy]	$T_j = 25^{\circ}C$		3.4	3.4	mJ
	Reverse Recovery Energy	$T_{j} = 150^{\circ}$	$T_{j} = 150^{\circ}C$		8		1113



Thermal and package characteristics

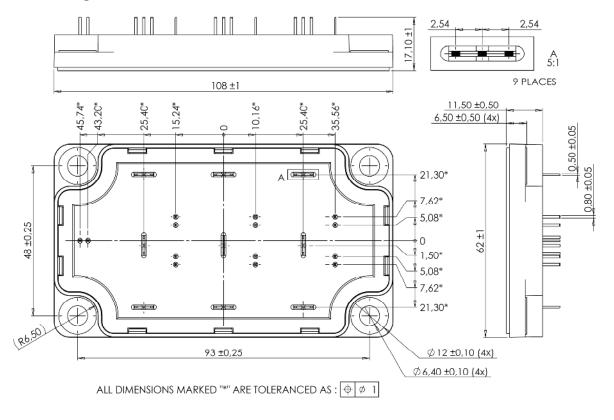
Symbol	Characteristic			Min	Тур	Max	Unit
D	Junction to Case Thermal Resistance		IGBT			0.29	°C/W
R _{thJC}	Junction to Case Thermal Resistance	Diode				0.5	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range			-40		175	
T _{STG}	Storage Temperature Range		-40		125	°C	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight				250	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic			Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C				50		kΩ
$\Delta R_{25}/R_{25}$					5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$				3952		Κ
$\Delta B/B$			T _C =100°C		4		%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP6-P Package outline (dimensions in mm)

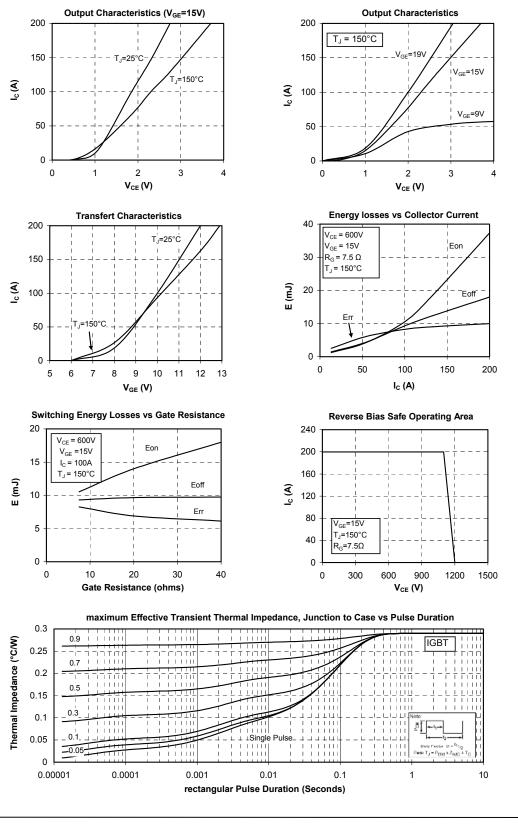


See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

www.microsemi.com



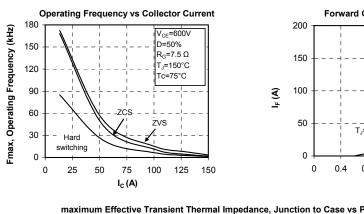
Typical Performance Curve

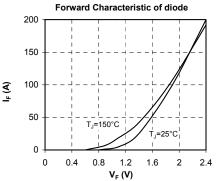


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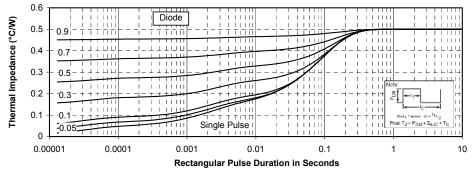
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maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration





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